MOS FET Power Amplifier Module for E-GSM Handy Phone



ADE-208-433C (Z) 4th Edition February 1997

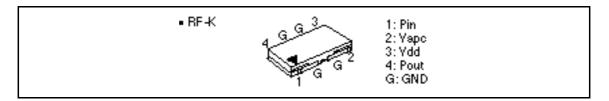
Application

- For E-GSM class4 880 to 915 MHz
- For 4.8V nominal battery use

Features

- High gain 3stage amplifier : 0 dBm input
- Lead less thin & Small package : 2 mm Max, 0.2cc
- High efficiency : 45% Typ at 3.8 W
- Wide gain control range : 90 dB Typ

Pin Arrangement



Absolute Maximum Ratings ($Tc = 25^{\circ}C$)

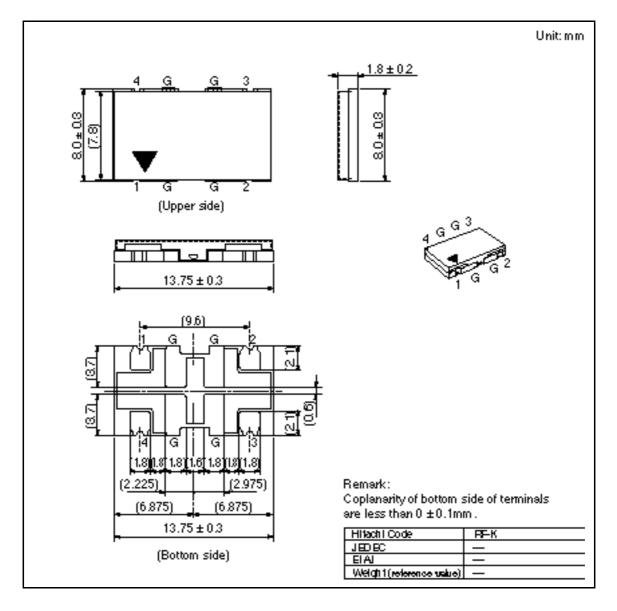
ltem	Symbol	Rating	Unit	
Supply voltage	V _{dd}	10	V	
Supply current	I _{DD}	3	А	
V _{APC} voltage	V _{APC}	4	V	
Input power	Pin	10	mW	
Operating case temperature	Tc (op)	-30 to +100	°C	
Storage temperature	Tstg	-30 to +100	°C	
Output power	Pout	5	W	



Item	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	880	—	915	MHz	
Control voltage range	V_{APC}	0.5	_	3.0	V	
Drain cutoff current	I _{DS}	_	_	100	μA	$V_{DD} = 10 \text{ V}, V_{APC} = 0 \text{ V}$
Total efficiency	т	40	45	—	%	$Pin = 1 \text{ mW}, V_{DD} = 4.8 \text{ V},$
2nd harmonic distortion	2nd H.D.	_	-45	-35	dBc	Pout = 3.8 W, Vapc = controlled
3rd harmonic distortion	3rd H.D.		-45	-35	dBc	$R_{L} = Rg = 50$, $Tc = 25^{\circ}C$
Input VSWR	VSWR (in)	_	1.5	3	—	
Output power (1)	Pout (1)	3.8	4.3	_	W	$\label{eq:prod} \begin{array}{l} \mbox{Pin} = 1 \mbox{ mW}, V_{\mbox{\tiny DD}} = 4.8 \mbox{ V}, \\ V_{\mbox{\tiny APC}} = 3.0 \mbox{ V}, R_{\mbox{\tiny L}} = Rg = 50 , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array}$
Output power (2)	Pout (2)	2.5	2.9	_	W	$ \begin{array}{l} \mbox{Pin} = 1 \mbox{ mW}, \mbox{ V}_{\mbox{\tiny DD}} = 4.3 \mbox{ V}, \\ \mbox{ V}_{\mbox{\tiny APC}} = 3.0 \mbox{ V}, \mbox{ R}_{\mbox{\tiny L}} = \mbox{Rg} = 50 \mbox{ ,} \\ \mbox{Tc} = 80^{\circ}\mbox{C} \end{array} , $
Isolation	_	_	-50	-40	dBm	$\label{eq:prod} \begin{array}{l} \mbox{Pin} = 1 \mbox{ mW}, V_{\mbox{\tiny DD}} = 4.8 \mbox{ V}, \\ V_{\mbox{\tiny APC}} = 0.5 \mbox{ V}, R_{\mbox{\tiny L}} = Rg = 50 , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array}$
Switching time	tr, tf	_	1	2	μs	$\label{eq:point} \begin{array}{l} \mbox{Pin} = 1 \mbox{ mW}, \mbox{ V}_{\mbox{\tiny DD}} = 4.8 \mbox{ V}, \\ \mbox{Pout} = 3.8 \mbox{ W}, \mbox{ R}_{\mbox{\tiny L}} = \mbox{Rg} = 50 \ , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array}$
Stability & Load VSWR tolerance	-	No parasitic oscillation & No degradation				$\begin{array}{l} \mbox{Pin}=1\mbox{ mW},\mbox{ V}_{\mbox{\tiny DD}}=4\mbox{ to }7\mbox{ V},\\ \mbox{Pout} 3.8\mbox{ W},\\ \mbox{Vapc} 3\mbox{ V}\mbox{ GSM}\mbox{ pulse}.\\ \mbox{Rg}=50\ ,\mbox{ t}=20\mbox{sec.},\mbox{ Tc}=25\mbox{°C},\\ \mbox{Output}\mbox{ VSWR}=6\mbox{ : 1}\mbox{ All phases} \end{array}$

Electrical Characteristics ($Tc = 25^{\circ}C$)

Package Dimensions



When using this document, keep the following in mind:

- 1. This document may, wholly or partially, be subject to change without notice.
- 2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
- 3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
- 4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
- 5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
- 6. MEDICAL APPLICATIONS: Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.

Semiconductor & IC Diu Nippon Bidg., 2-6-2, Oht-machi, Chiyoda-ku, Tokyo 100, Japan Tel: Tokyo (08)8270-2111 Fan: (08)8270-5109

For further information write to:

Hitschi America, Ltd. Semiconductor & IC Diu 2000 Sterra Point Patuway: Brisbane, CA 94005-1885 US A Tel: 415-589-8800 Fail: 415-589-8800 Hilachi Europe GmbH Beatronic Components Group Continental Europe Domacher Straße 8 D-85622 Feldkirchen München Tel: 089-9 91 80-0 Fau: 089-9 29 80 00 Hilachi Burope Lti. Bectronic Components Di u Northern Europe Headquariers Vittebrook Park Lower Cookham Road Maldenhead Berkshte 816 8YA United Kingdom Tel: 0608-585000 Fai: 0608-778800 Hilachi Asia Pie, Ltd. 16 Collyer Quay/#20-00 Hilachi Tomer Singapore 0104 Tel: 585-2100 Fau: 585-1588

Hilachi Asia (Hong Kong) Ltd. Unit 706, North Tomer, Verki Rinance Centre, Harbour City Canton Road Tsim Sha Tsul, Komioon Hong Kong Tel: 27859218 Fai: 27806071

Copyright © Hitachi, Ltd., 1997. All rights reserved. Rinted in Japan.

HITACHI